



NPN Epitaxial Silicon Transistor

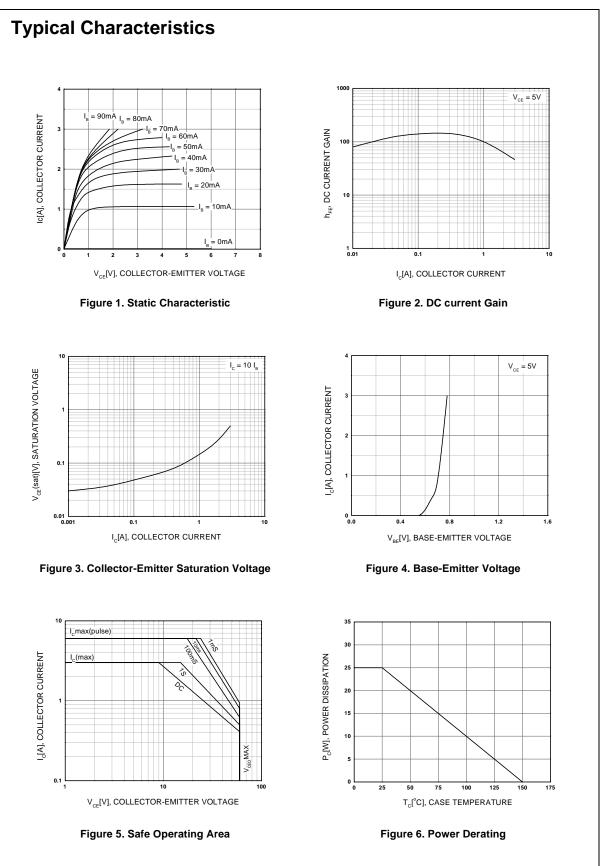
Absolute Maximum Ratings Tc=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	60	V
V _{EBO}	Emitter-Base Voltage	7	V
IC	Collector Current	3	A
IB	Base Current	0.5	A
P _C	Collector Dissipation (T _C =25°C)	25	W
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

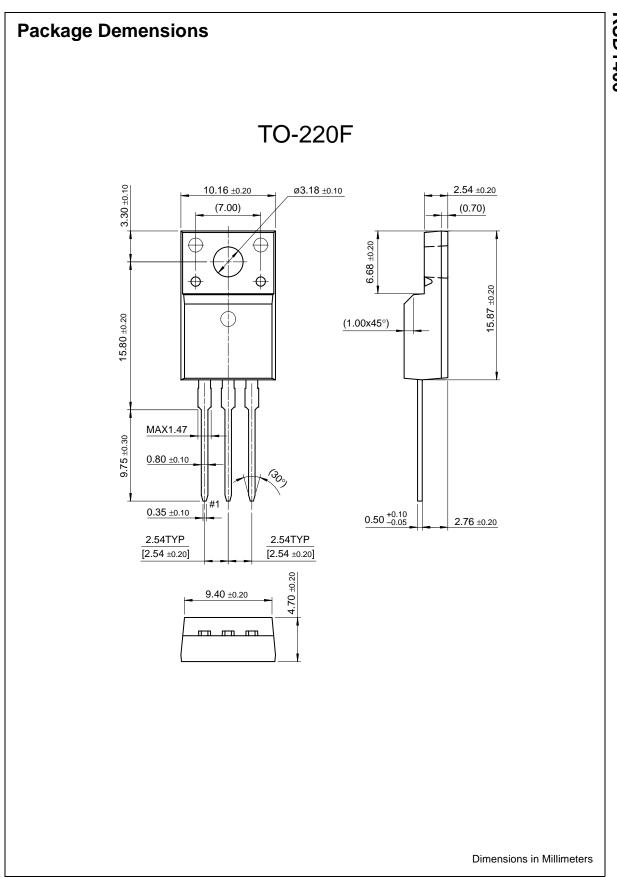
Electrical Characteristics Tc=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 50mA, I _B = 0	60			V
I _{CBO}	Collector Cut-off Current	$V_{CB} = 60V, I_E = 0$			100	μA
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 7V, I_{C} = 0$			100	μA
h _{FE1} h _{FE2}	DC Current Gain	$V_{CE} = 5V, I_C = 0.5A$ $V_{CE} = 5V, I_C = 3A$	60 20		300	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = 3A, I _B = 0.3A		0.4	1	V
V _{BE} (on)	Base-Emitter ON Voltage	$V_{CE} = 5V, I_{C} = 0.5A$	1.00	0.7	1	V
f _T	Current Gain Bandwidth Product	V _{CE} = 5V, I _C = 0.5A	28	3		MHz
C _{ob}	Output Capacitance	V _{CB} = 10V, f = 1MHz	3.0.	70	10-	pF
t _{ON}	Turn ON Time	$V_{CC} = 30V, I_{C} = 1A$		0.8		μs
t _{STG}	Storage Time	$I_{B1} = -I_{B2} = 0.2A$		1.5		μs
t _F	Fall Time	$R_{L} = 30\Omega$		0.8		μs

h _{FE1} Classification					
Classification	0	Y	G		
h _{FE1}	60 ~ 120	100 ~ 200	150 ~ 300		



KSD1406



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